

< Power GaAs FET >

MGF1941AL

Micro-X type plastic package

DESCRIPTION

The MGF1941AL power MES FET is designed for use in S to Ku band power amplifiers.

FEATURES

High gain and High P1dB P1dB=15dBm, Glp=10 dB (Typ.) @ f=12GHz

APPLICATION

S to Ku band low noise amplifiers

QUALITY GRADE

GG

RECOMMENDED BIAS CONDITIONS

VDS=3V, ID=30mA

ORDERING INFORMATION

Tape & reel 4,000pcs/reel

Rohs Compliant

MGF1941AL is a RoHS compliant product. RoHS compliance is indicated by the letter "G" after the Lot Marking.

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

| Symbol | Parameter | Ratings | Unit |
|------------------|-------------------------|-------------|------|
| VGDO | Gate to drain voltage | -5 | V |
| VGSO | Gate to source voltage | -5 | V |
| ID | Drain current | 120 | mA |
| PT | Total power dissipation | 300 | mW |
| T _{ch} | Channel temperature | 175 | °C |
| T _{stg} | Storage temperature | -65 to +150 | °C |
| rstg | Storage temperature | -05 (0 +150 | , C |

ELECTRICAL CHARACTERISTICS (Ta=25°C)

| Symbol | Parameter | Test conditions | Limits | | | Unit |
|----------------------|---------------------------------|--------------------|--------|------|------|------|
| | | | MIN. | TYP. | MAX | |
| $V_{(BR)GDO}$ | Gate to drain breakdown voltage | IG=-30μA | -8 | -15 | | V |
| I _{DSS} | Saturated drain current | VGS=0V,VDS=3V | 35 | 60 | 120 | mA |
| V _{GS(off)} | Gate to source cut-off voltage | VDS=3V,ID=300μA | -0.3 | -1.4 | -3.5 | V |
| P1dB | Output power at 1dB gain | VDS=3V, ID=30mA, | 11 | 15 | | dBm |
| | compression | f=12GHz | | | | |
| Glp | Linear power gain | VDS=3V, ID=30mA, | 7 | 10 | | dB |
| | | f=12GHz, Pin=-5dBm | | | | |
| Gs | Associated gain | VDS=3V, ID=10mA, | | 9 | | dB |
| NFmin | Minimum noise figure | f=12GHz | | 1.2 | | dB |

Note: P1B and Glp are tested with sampling inspection.

Gs/NFmin are not tested.

Outline Drawing

MITSUBISHI Proprietary

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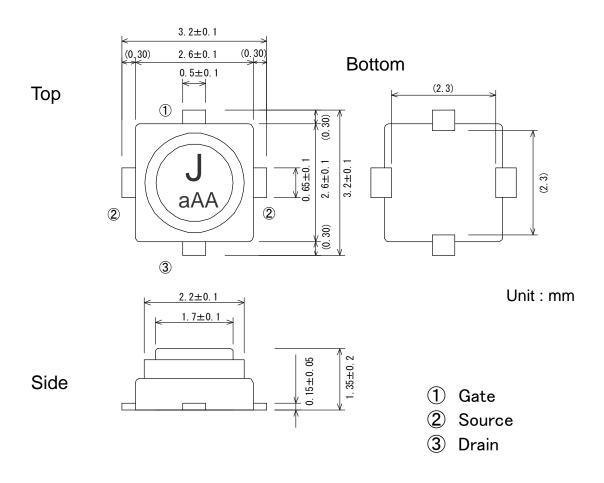
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Fig.1

Publication Date: Mar., 2012

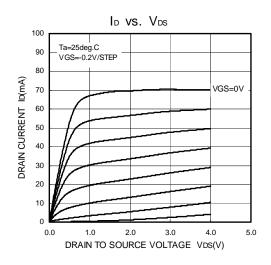
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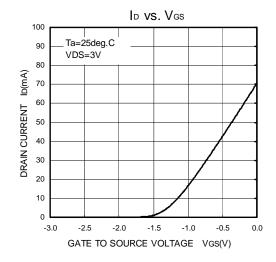
Fig.1

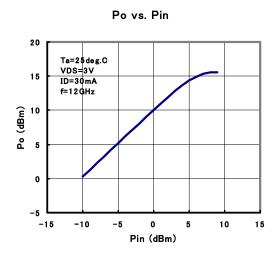


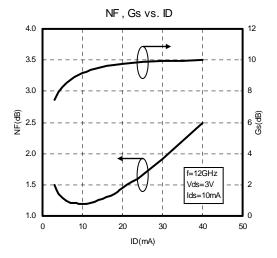
(GD-32)

TYPICAL CHARACTERISTICS (Ta=25°C)





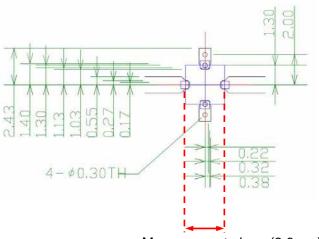




S PARAMETERS

(Conditions:VDS=3V,ID=30mA,Ta=25deg.C)

| f | S11 | | S21 | | S12 | | S22 | | K | MAG/MSG |
|-------|-------|--------|-------|--------|-------|-------|-------|--------|------|---------|
| (GHz) | Mag. | Angle | Mag. | Angle | Mag. | Angle | Mag. | Angle | | (dB) |
| 1 | 0.981 | -20.3 | 5.081 | 159.6 | 0.016 | 78.2 | 0.567 | -11.2 | 0.21 | 25.0 |
| 2 | 0.933 | -40.4 | 4.936 | 140.0 | 0.031 | 67.1 | 0.549 | -22.2 | 0.38 | 22.0 |
| 3 | 0.862 | -60.6 | 4.742 | 120.8 | 0.045 | 56.7 | 0.520 | -32.9 | 0.54 | 20.3 |
| 4 | 0.780 | -81.1 | 4.509 | 102.2 | 0.056 | 47.1 | 0.482 | -43.4 | 0.70 | 19.1 |
| 5 | 0.694 | -102.4 | 4.265 | 84.0 | 0.066 | 38.0 | 0.440 | -53.8 | 0.85 | 18.1 |
| 6 | 0.610 | -124.3 | 3.982 | 66.6 | 0.073 | 30.2 | 0.394 | -63.2 | 1.00 | 17.4 |
| 7 | 0.547 | -149.6 | 3.689 | 49.0 | 0.079 | 22.2 | 0.340 | -76.0 | 1.12 | 14.6 |
| 8 | 0.499 | -174.0 | 3.389 | 32.7 | 0.083 | 14.8 | 0.288 | -87.7 | 1.27 | 13.0 |
| 9 | 0.480 | 162.9 | 3.117 | 17.6 | 0.087 | 9.4 | 0.243 | -100.4 | 1.37 | 11.9 |
| 10 | 0.480 | 142.0 | 2.904 | 3.5 | 0.091 | 5.7 | 0.209 | -114.9 | 1.43 | 11.1 |
| 11 | 0.505 | 123.1 | 2.720 | -10.8 | 0.098 | 1.6 | 0.185 | -135.0 | 1.39 | 10.7 |
| 12 | 0.548 | 106.4 | 2.569 | -25.2 | 0.107 | -3.6 | 0.177 | -162.1 | 1.29 | 10.6 |
| 13 | 0.588 | 90.2 | 2.393 | -39.4 | 0.113 | -10.5 | 0.176 | 168.8 | 1.24 | 10.3 |
| 14 | 0.633 | 76.4 | 2.277 | -53.3 | 0.122 | -16.3 | 0.215 | 147.8 | 1.11 | 10.7 |
| 15 | 0.670 | 62.2 | 2.142 | -69.1 | 0.131 | -24.9 | 0.287 | 125.6 | 1.00 | 11.8 |
| 16 | 0.722 | 53.0 | 1.968 | -84.2 | 0.135 | -33.3 | 0.354 | 103.6 | 0.90 | 11.6 |
| 17 | 0.761 | 41.1 | 1.799 | -98.6 | 0.140 | -40.8 | 0.423 | 88.8 | 0.82 | 11.1 |
| 18 | 0.788 | 30.8 | 1.614 | -113.4 | 0.143 | -49.7 | 0.506 | 74.5 | 0.74 | 10.5 |



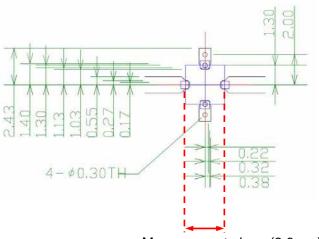
Measurement plane (2.6mm)

Recommended foot pattern; RO4003C/Rogers (εr=3.38, t=0.508mm)

S PARAMETERS

(Conditions:VDS=3V,ID=10mA,Ta=25deg.C)

| f | S11 | | S21 | | S12 | | S22 | | K | MAG/MSG |
|-------|-------|--------|-------|--------|-------|-------|-------|--------|------|---------|
| (GHz) | Mag. | Angle | Mag. | Angle | Mag. | Angle | Mag. | Angle | | (dB) |
| 1 | 0.988 | -17.8 | 3.647 | 161.6 | 0.019 | 77.8 | 0.625 | -11.5 | 0.16 | 22.8 |
| 2 | 0.955 | -35.7 | 3.602 | 143.8 | 0.038 | 66.0 | 0.609 | -23.0 | 0.29 | 19.8 |
| 3 | 0.907 | -54.0 | 3.549 | 125.9 | 0.054 | 54.5 | 0.581 | -34.5 | 0.41 | 18.1 |
| 4 | 0.845 | -73.0 | 3.478 | 108.0 | 0.069 | 43.2 | 0.544 | -46.1 | 0.54 | 17.0 |
| 5 | 0.776 | -92.9 | 3.394 | 90.2 | 0.081 | 32.1 | 0.498 | -57.9 | 0.66 | 16.2 |
| 6 | 0.698 | -113.8 | 3.266 | 72.6 | 0.090 | 21.8 | 0.445 | -69.2 | 0.81 | 15.6 |
| 7 | 0.629 | -138.1 | 3.101 | 54.1 | 0.096 | 11.1 | 0.384 | -83.6 | 0.95 | 15.1 |
| 8 | 0.570 | -161.9 | 2.904 | 37.0 | 0.098 | 1.1 | 0.325 | -97.2 | 1.12 | 12.6 |
| 9 | 0.535 | 174.6 | 2.706 | 21.0 | 0.097 | -6.2 | 0.272 | -111.8 | 1.29 | 11.2 |
| 10 | 0.522 | 153.1 | 2.535 | 5.8 | 0.094 | -10.7 | 0.234 | -127.8 | 1.45 | 10.3 |
| 11 | 0.534 | 132.8 | 2.382 | -9.3 | 0.095 | -13.9 | 0.211 | -148.2 | 1.51 | 9.8 |
| 12 | 0.568 | 114.5 | 2.249 | -24.4 | 0.099 | -17.3 | 0.207 | -173.7 | 1.46 | 9.6 |
| 13 | 0.604 | 97.1 | 2.091 | -39.2 | 0.101 | -22.4 | 0.212 | 159.9 | 1.44 | 9.2 |
| 14 | 0.642 | 82.1 | 1.981 | -53.6 | 0.107 | -25.9 | 0.250 | 140.7 | 1.32 | 9.3 |
| 15 | 0.673 | 67.1 | 1.844 | -69.7 | 0.114 | -32.4 | 0.322 | 120.7 | 1.20 | 9.4 |
| 16 | 0.724 | 57.1 | 1.685 | -84.9 | 0.118 | -39.5 | 0.386 | 99.9 | 1.06 | 10.0 |
| 17 | 0.761 | 44.9 | 1.531 | -99.4 | 0.122 | -45.4 | 0.450 | 85.7 | 0.96 | 11.0 |
| 18 | 0.787 | 34.2 | 1.364 | -114.1 | 0.126 | -53.4 | 0.528 | 72.0 | 0.86 | 10.3 |



Measurement plane (2.6mm)

Recommended foot pattern; RO4003C/Rogers (εr=3.38, t=0.508mm)

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